

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.0 -4.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-7.2 -5.7	A
Continuous Drain Current (Note 6) V _{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-5.2 -4.1	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-6.2 -4.9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-24	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	106	°C/W
	t < 10s		74	
Total Power Dissipation (Note 6)		P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	65	°C/W
	t < 10s		46	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	11.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-0.7	-1.5	V	V _{DS} = V _{GS} , I _D = -250μA
Gate Threshold Voltage Temperature Coefficient	ΔV _{GS(TH)} /ΔT _J	—	2.5	—	mV/°C	I _D = -250μA, Referenced to +25°C
Static Drain-Source On-Resistance	R _{DS(ON)}	—	23	35	mΩ	V _{GS} = -4.5V, I _D = -4.0A
		—	30	45		V _{GS} = -2.5V, I _D = -4.0A
		—	41	62		V _{GS} = -1.8V, I _D = -2.0A
Forward Transfer Admittance	Y _{fs}	—	18	—	S	V _{DS} = -5V, I _D = -5.5A
Diode Forward Voltage (Note 6)	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1,610	2,400	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	157	210		
Reverse Transfer Capacitance	C _{rss}	—	145	200		
Gate Resistance	R _G	—	9.4	14.1	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	15.4	23.1	nC	V _{DS} = -10V, V _{GS} = -4.5V I _D = -4A
Gate-Source Charge	Q _{gs}	—	2.5	—		
Gate-Drain Charge	Q _{gd}	—	3.3	—		
Turn-On Delay Time	t _{D(ON)}	—	17	33	ns	V _{GS} = -4.5V, V _{DS} = -10V, R _G = 6Ω, I _D = -1A, R _L = 10Ω
Turn-On Rise Time	t _R	—	12	19		
Turn-Off Delay Time	t _{D(OFF)}	—	94	150		
Turn-Off Fall Time	t _F	—	42	64		
Reverse Recovery Time	t _{RR}	—	14	25	ns	I _F = -4.5A, di/dt = 100A/μS
Reverse Recovery Charge	Q _{RR}	—	4	8	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

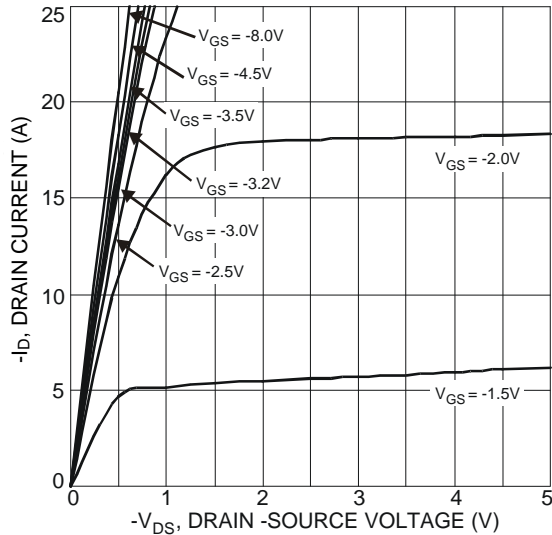


Fig. 1 Typical Output Characteristics

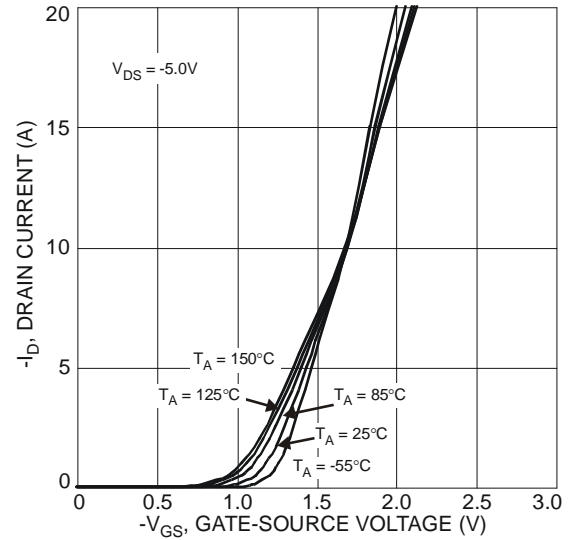


Fig. 2 Typical Transfer Characteristics

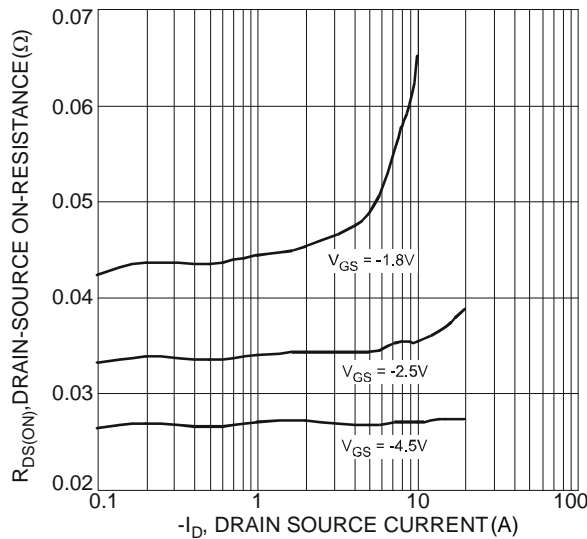


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

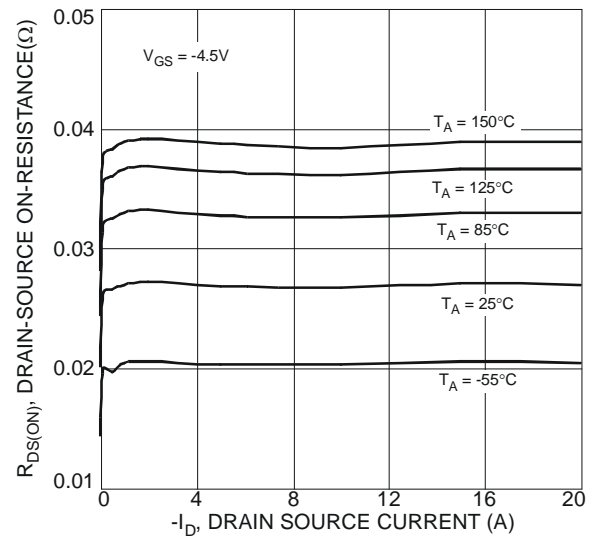


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

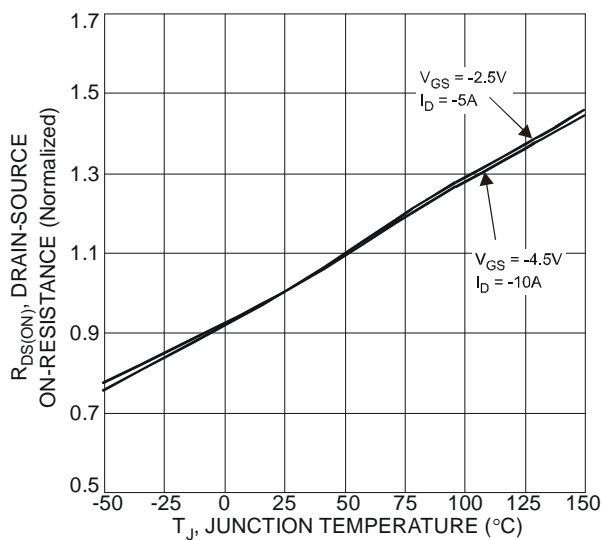


Fig. 5 On-Resistance Variation with Temperature

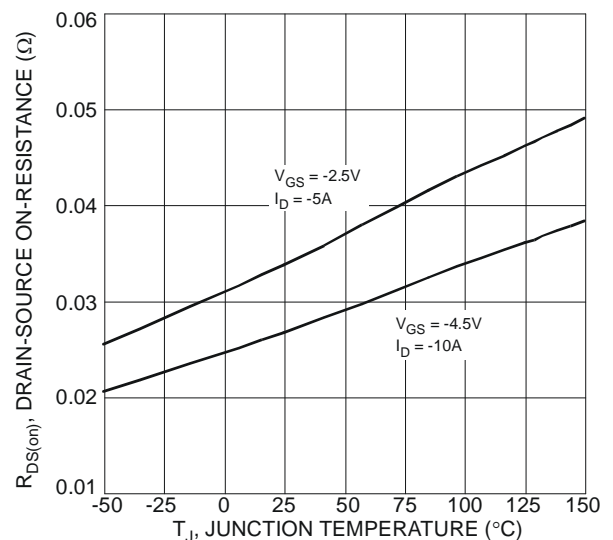


Fig. 6 On-Resistance Variation with Temperature

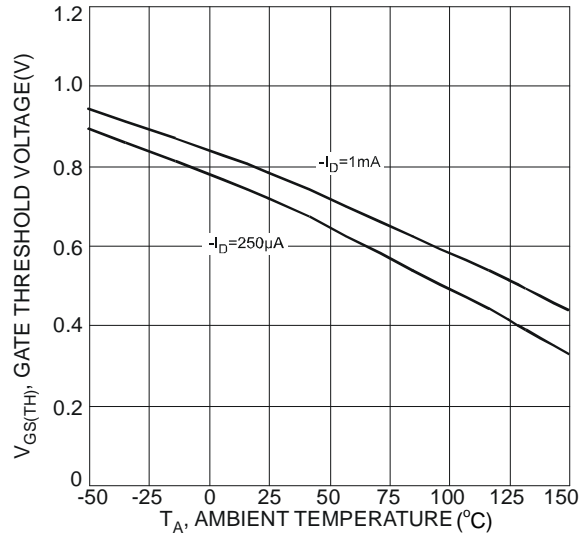


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

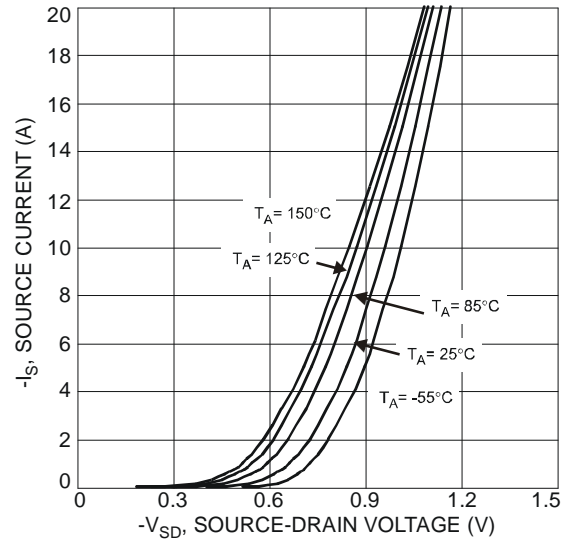


Fig. 8 Diode Forward Voltage vs. Current

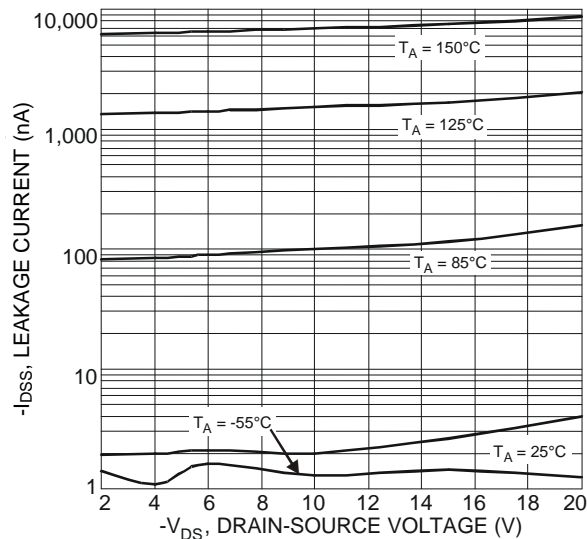


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

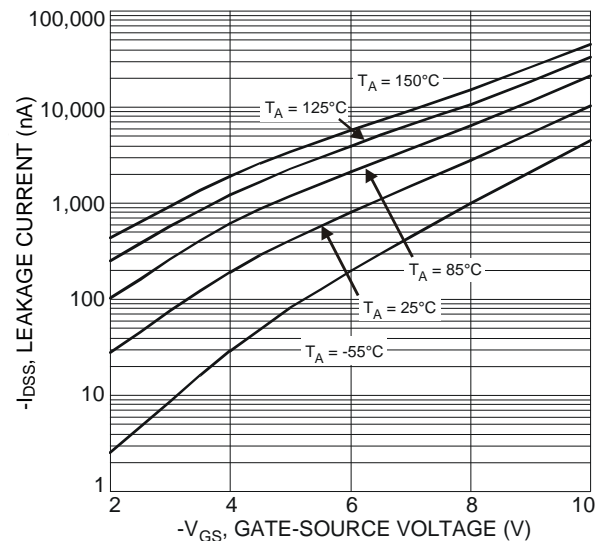


Fig. 10 Typical Gate-Source Leakage Current vs. Voltage

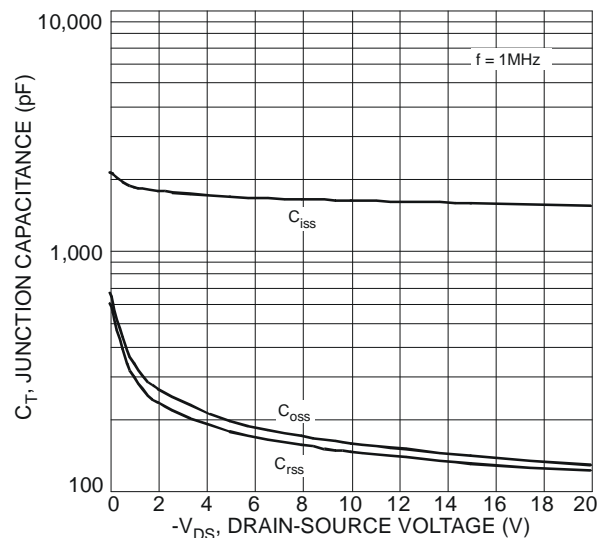


Fig. 11 Typical Junction Capacitance

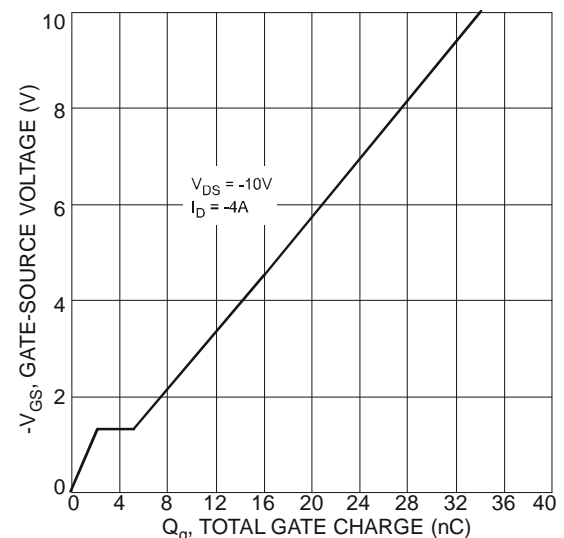


Fig. 12 Gate-Charge Characteristics

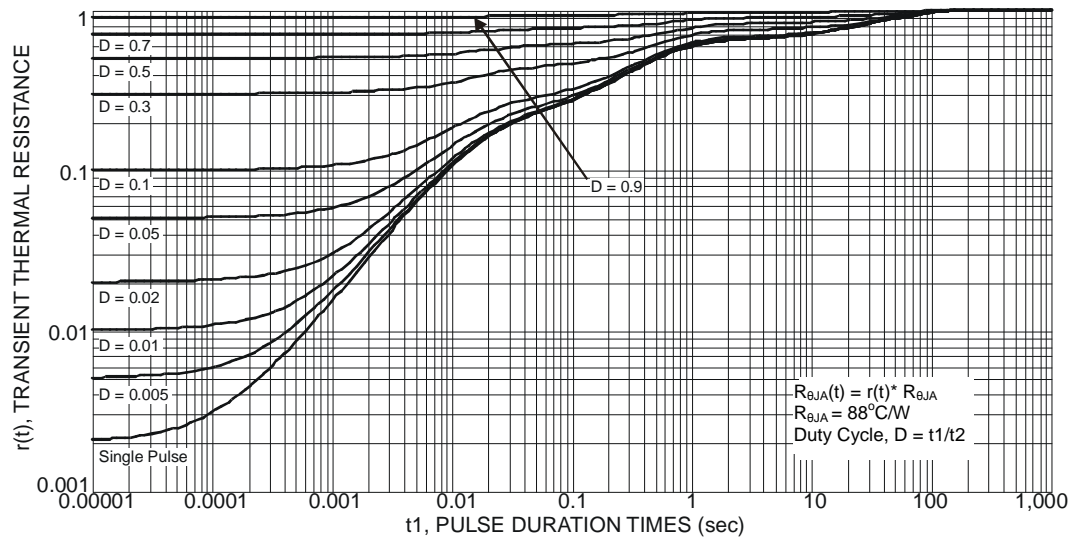
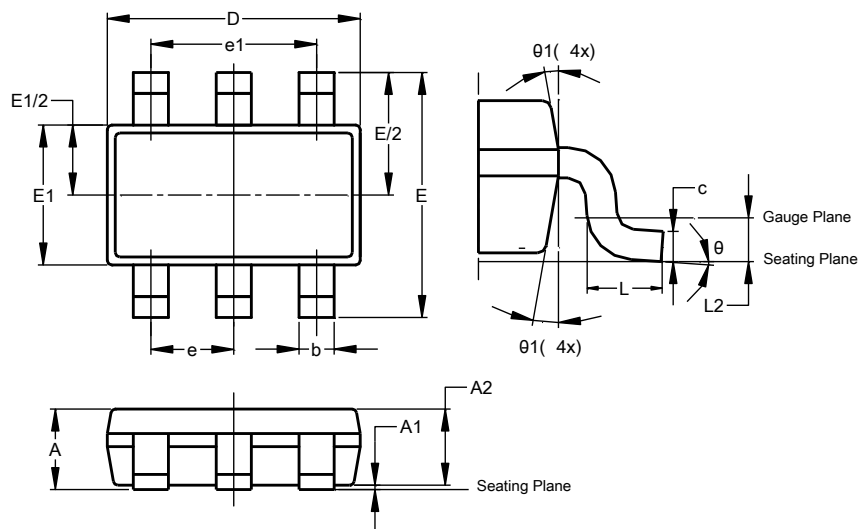


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

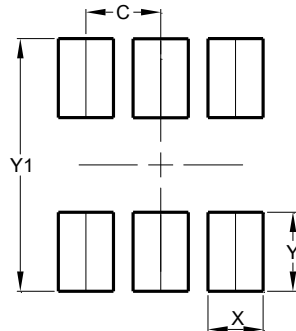


TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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